

RAA23021x

R18DS0013EJ0101 Rev. 1.01 Jan 17, 2014

5.5V Input, 3A, Step-Down DC/DC Converter + LDO

Description

The RAA23021x is a high efficiency monolithic step-down DC/DC synchronous converter plus a LDO (low dropout) regulator which has an ultra-low power mode.

Features

- DC/DC converter (ch1)
 - Synchronous rectification type step-down circuit
 - Integrated power MOSFETs
 - Preset output voltage (There are also products that have adjustable output voltage using external resistors.)
 - Internal phase compensator
 - Switching frequency: 1 MHz (fixed)
 - Internal timer-latch-type short-circuit protector (fixed delay time)
 - 100% duty cycle operation
- LDO (ch2)
 - 500mA
 - Internal over current protector (foldback-current limiting)
 - Ultra low-power save mode (25uA typical)
- Common Features
 - Internal rise up sequencer
 - Internal digital soft-start function (2 ms fixed soft-start time)
 - Internal discharge circuit
 - Power good function
 - Internal timer-latch-type thermal shutdown circuit (shutdown temperature: 150°C or higher)
 - Internal recovery-type under voltage lockout circuit

Application

- Communication
- Industrial
- Building
- Smart meter

And, usable around MCU, ASIC, FPGA, etc.

Ordering Information

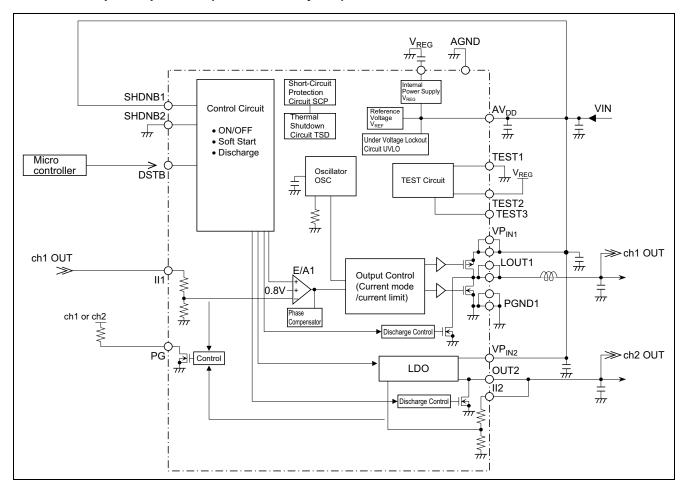
Ordering Part No.	Package	Tape and Reel
RAA230211GSB#HA0	20-pin HTSSOP	Embossed taping. 2,500pcs/reel
RAA230212GSB#HA0		
RAA230213GSB#HA0		
RAA230214GSB#HA0		
RAA230215GSB#HA0		

Part No Summary

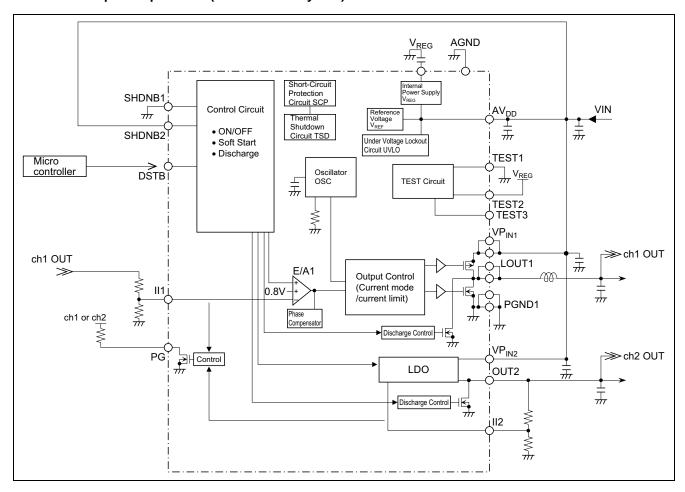
		Input	Output Voltage		Maximum	Switching	
Part No.	Output	Voltage	ch1	ch2	Output Current	Frequency	Package
RAA230211GSB	ch1:DC/DC	3.0 V	1.8	1.8	ch1:3 A	1 MHz	20-pin
RAA230212GSB	(step-down,	to	2.7	2.7	ch2:0.5 A	(fixed)	HTSSOP
RAA230213GSB	current mode)	5.5 V	3.0	3.0			
RAA230214GSB	ch2:LDO		3.3	3.3			
RAA230215GSB	=		0.9 V to VI	N×0.8			
			(Adjustable	e each			
			output indi	vidually			
			by external	resistor)			

Application Circuit Example

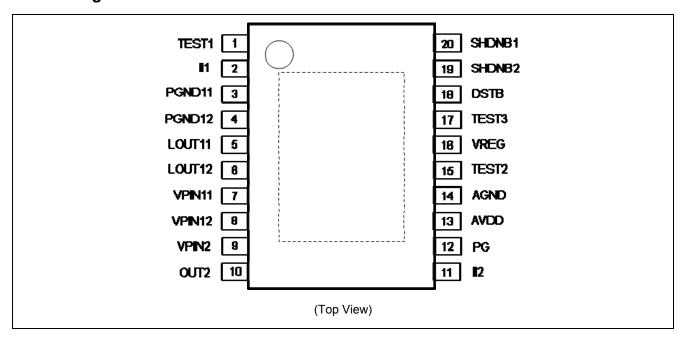
ch1/ch2: Preset output voltage by internal resistor. Sequence pattern 1 (ch1 followed by ch2)



ch1/ch2: Adjustable output voltage by external resistor.
Sequence pattern 2 (ch2 followed by ch1)



Pin Configuration



Pin Function

Pin No.	Symbol	I/O	Function
1	TEST1	_	Test pin 1 (connect to AGND)
2	II1	Input	Inverted input for error amplifier of ch1
3	PGND11	Ground	Power ground
4	PGND12	Ground	Power ground
5	LOUT11	Output	Inductor connection 1 for ch1
6	LOUT12	Output	Inductor connection 2 for ch1
7	VP _{IN11}	Power supply	Output stage power input 1 of ch1
8	VP _{IN12}	Power supply	Output stage power input 2 of ch1
9	VP _{IN2}	Power supply	Output stage power input of ch2
10	OUT2	Output	Output of ch2
11	II2	Input	Inverted input for error amplifier of ch2
12	PG	Output	Power-good output (open-drain)
13	AV_{DD}	Power supply	Analog block power supply
14	AGND	Ground	Analog ground
15	TEST2	_	Test pin 2 (connect to V _{REG})
16	V_{REG}	Output	Internal power supply output (connect 1uF)
17	TEST3	_	Test pin 3 (open)
18	DSTB	Input	Light-load operation mode setting pin
19	SHDNB2	Input	Output ON/OFF of ch2
20	SHDNB1	Input	Output ON/OFF of ch1

Absolute Maximum Ratings

(Unless otherwise specified, $T_A = 25^{\circ}C$)

Parameter	Symbol	Ratings	Unit	Condition
Analog power supply (AV _{DD} pin)	AV_{DD}	-0.5 to +6.5	V	AV_{DD}
VP _{IN} pin applied voltage	VP _{IN}	-0.5 to +6.5	V	VP _{IN11} , VP _{IN12} , VP _{IN2}
SHDNB pin applied voltage	V _{SHDNB}	-0.5 to +6.5	V	SHDNB1, SHDNB2
DSTB pin applied voltage	V_{DSTB}	-0.5 to +6.5	V	DSTB
PG pin applied voltage	V_{PG}	-0.5 to +6.5	V	PG
Il pin applied voltage	VII	-0.5 to +6.5	V	II1, II2
VP _{IN11} +VP _{IN12} pin sink current (peak)	IP _{IN1(peak)}	3500	mA	VP _{IN11} +VP _{IN12}
LOUT11+LOUT12 pin output source	I _{LO1(peak)+}	3500	mA	LOUT11, LOUT12
current (peak)				
VP _{IN2} pin sink current (DC)	IP _{IN2(DC)}	500	mA	VP _{IN2}
OUT2 pin output source current (DC)	I _{O2(DC)+}	500	mA	OUT2
LOUT11+LOUT12, OUT2 pin output	I _{LO1,O2(DC)}	100	mA	when discharge circuit is
source current (DC)				operation.
Total power dissipation	P _T	3400 ^{*1}	mW	T _A ≤ +25°C
Operating ambient temperature	T _A	-40 to +85	°C	
Junction temperature	TJ	-40 to +150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note:

Board specification: 4-layers glass epoxy board, 76.2mm x 114.3mm x 1.664mm.

Copper coverage area: 50%, 0.070mm thickness (top and bottom layers)

95%, 0.035mm thickness (layers 2 and 3).

Connecting exposed pad

Caution: Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Recommended Operating Condition

(Unless otherwise specified, $T_A = 25^{\circ}C$)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Analog power supply voltage	AV_{DD}	3.0	5.0	5.5	V	AV _{DD}
(AV _{DD} pin)						
VP _{IN} pin applied voltage	VP _{IN}	_	AV_{DD}	_	V	VP _{IN11} , VP _{IN12} , VP _{IN2}
SHDNB pin applied voltage	V _{SHDNB}	0	_	AV_DD	V	SHDNB1, SHDNB2
DSTB pin applied voltage	V_{DSTB}	0	_	AV_DD	V	DSTB
PG pin applied voltage	V_{PG}	0	_	AV_DD	V	PG
II pin applied voltage	VII	0	_	AV_DD	V	II1, II2
V _{REG} pin capacitance	C _{REG}	_	1.0	_	μF	V _{REG}
Operating junction temperature	T _{JO}	-40	_	+125	°C	

^{*1} This is the value at $T_A \le +25^{\circ}C$. At $T_A > +25^{\circ}C$, the total power dissipation is derated by 34mW/°C.

Electrical Characteristics

(Unless otherwise specified, $T_A = 25$ °C, $AV_{DD} = VP_{IN1} = VP_{IN2} = 5.0 \text{ V}$, VOUT2 = 3.3 V, $f_{OSC} = 1 \text{ MHz}$, DSTB = L)

`	Parameter	Symbol	Min	Typ	Max	Unit	Condition
Total	Standby current	I _{DD(STNBY)}	_	1	2	μА	Al _{DD} +IP _{IN1} +IP _{IN2}
Total	Claridady Gurrent	IDD(STNBY)		•		μ. τ	SHDNB1 = SHDNB2 = AGND
	Circuit operation current 1	I _{DD1}	_	1.2	2	mA	AI_{DD} , SHDNB1 = SHDNB2 = AV_{DD} DSTB = GND (normal mode)
	Circuit operation current 2	I _{DD2}	_	25	40	μА	AI _{DD} , SHDNB1 = SHDNB2 = AV _{DD} DSTB = AV _{DD} (ultra low-power mode)
Internal power supply block (V _{REG})	Internal power supply voltage	V _{REG}	2.3	2.4	2.5	V	I _{REG} = 0mA
Under voltage lock	Operation start voltage during rise time	$AV_{DD(L-H)}$	2.7	2.9	3.0	V	AV _{DD} pin voltage is detected
out circuit (UVLO)	Operation stop voltage	$AV_{DD(H-L)}$	2.6	2.8	3.0	V	AV _{DD} pin voltage is detected
Short-circuit protection	II1 input detection voltage (ch1)	V _{TH(II)1}	65	75	85	%	II1 pin, Ratio to the output voltage or E/A1 threshold voltage
circuit (SCP)	Delay time	t _(DLY)	_	10	20	ms	
Oscillation block	Oscillation frequency	fosc	_	1000	_	kHz	
Soft start block	Soft start time	t _{ss}	0.9	2.0	4.0	ms	ch1, ch2
PWM block	Maximum duty	D _{MAX.(PWM)}	_	100	_	%	ch1
Output	ch1 output voltage accuracy	V _{OUT1}	-2.5	_	+2.5	%	I _{O1} = 200mA, (with internal resistor)
voltage accuracy (with resistor inside)	ch2 output voltage accuracy	V _{OUT2}	– 1	_	+1	%	I _{O2} = 10mA, (with internal resistor)
E/A block (with resistor	E/A 1 input threshold voltage	V _{ITH1}	0.780	0.800	0.820	٧	Including input offset, (with external resistor)
outside)	E/A 2 input threshold voltage	V _{ITH2}	0.792	0.800	0.808	٧	Including input offset, (with external resistor)
Output block	P-ch ON resistance	R _{on-p1}	_	0.15	0.3	Ω	I _O = 100mA
	N-ch ON resistance	R _{on-n1}	_	0.15	0.3	Ω	I _O = -100mA
Discharging	ch1 ON resistance	R _{ondc1}	_	100	200	Ω	ch1, I _{DC} = 20mA
circuit block	ch2 ON resistance	R _{ondc2}	_	200	400	Ω	ch2, I _{DC} = 20mA
Series regulator	The voltage between the input and output	V _{DIF2}	0.5	_	_	V	I ₀₂ = 20mA
block (ch2,	Input regulation	REG _{IN2}	_	_	50	mV	I _{O2} = 20mA, VP _{IN} = 3.0V to 5.5V
DSTB =	Load regulation	REG _{L2}	_	_	50	mV	I _{O2} = 1mA to 500mA
AGND:	Output short-circuit current	I _{O2short}	_	100	1 –	mA	OUT2=AGND
normal mode)	Peak output current	I _{O2peak}	550	_	_	mA	
Series regulator	The voltage between the input and output	V_{DIF2}	0.5	_	_	٧	$I_{O2} = 10 \mu A$
block (ch2,	Input regulation	REG _{IN2}	_	_	100	mV	I_{02} = 10 μ A, VP _{IN} = 3.0V to 5.5V
DSTB = AV _{DD} : ultra low-power	Load regulation	REG _{L2}	_	_	100	mV	I _{O2} = 10μA to 50mA
mode)						l	

Electrical Characteristics (cont.)

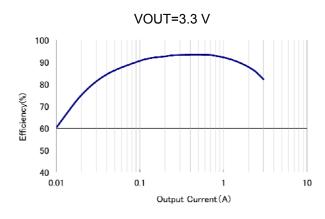
 $(Unless otherwise specified, \underline{T_A} = 25^{\circ}C, \ AV_{DD} = VP_{INI} = VP_{IN2} = 5.0 \ V, \ VOUT2 = 3.3 \ V, \ f_{OSC} = 1 \ MHz, \ DSTB = L)$

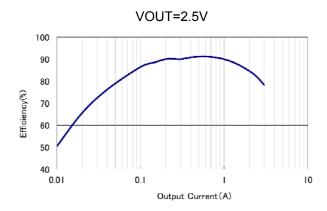
	Parameter	Symbol	Min	Тур	Max	Unit	Condition
Power-good	Threshold voltage	$V_{TH(PG)}$	86	90	94	%	PG = "HiZ"→"L", "L"→"HiZ"
circuit block							Ratio to the output voltage
	PG pin output voltage	V_{PG}	_	_	0.1	V	$I_{PG-} = 0.1 \text{mA}$
	PG pin leakage current	I _{LEAK-PG}	_	_	1	μА	SHDNB1, SHDNB2 = AGND
	Delay time	t _{DLY-PG}	_	_	2	ms	Time from detecting of output
							startup until change form L to HiZ
							on PG pin
ON/OFF	Threshold voltage	V _{TH}	0.6	_	1.4	V	SHDNB1, SHDNB2, DSTB
controller							
block							

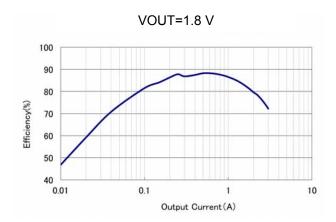
Typical Performance Characteristics

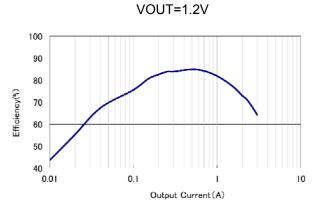
(Unless otherwise specified, $T_A = 25$ °C, $AV_{DD} = VP_{IN1} = VP_{IN2} = 5.0 \text{ V}$)

Efficiency vs. Output Current (ch1)



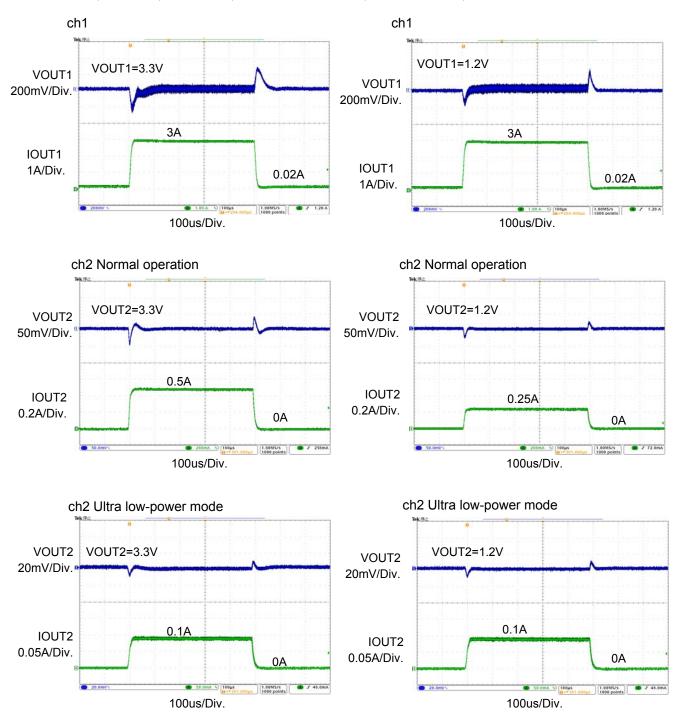




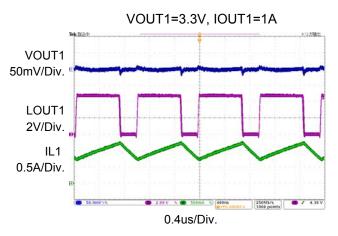


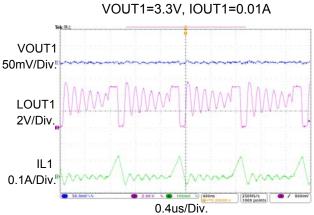
Load Step Transient Waveforms

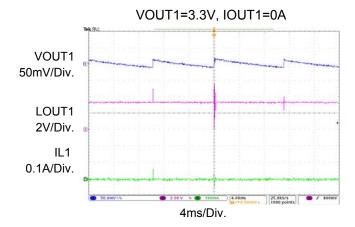
TA = 25°C, VIN = 5V, L1 = 2.2uH, CIN1 = CIN2 = 10uF, COUT1 = 20uF, COUT2 = 10uF



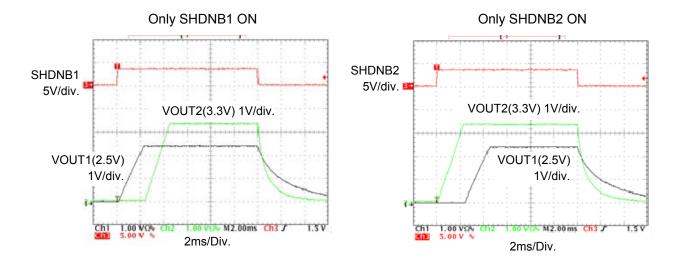
Ch1 Operation Waveforms



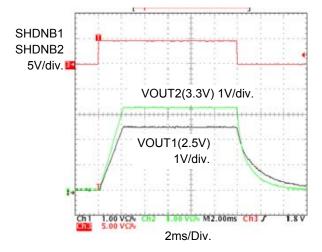




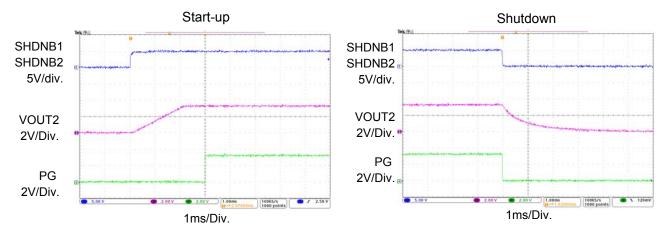
Start-up and Shutdown Waveforms



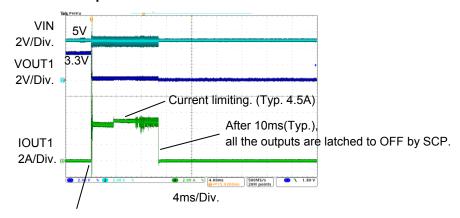
Both SHDNB1 and SHDNB2 ON at the same time



Power Good Waveform *PG pin is connected to ch2 output(3.3V)

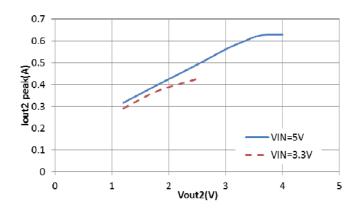


Short-circuit protection waveform

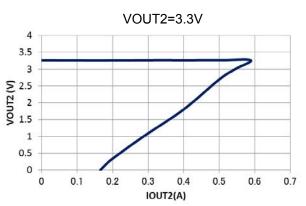


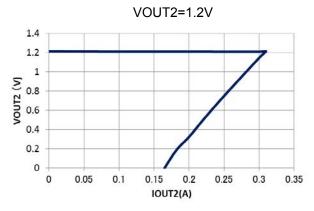
Ch1 output short-circuits.

Ch2(LDO) peak output current vs. output voltage (VIN=5.0V)

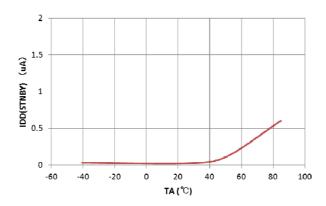


Ch2(LDO) output voltage vs. output current (VIN=5.0V)





Standby current vs. Operating ambient temperature



IC Surface Temperature vs. Time

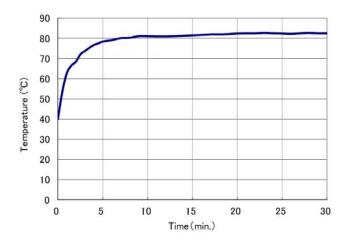
Ch1 and ch2 operation (normal mode)

VIN=5V

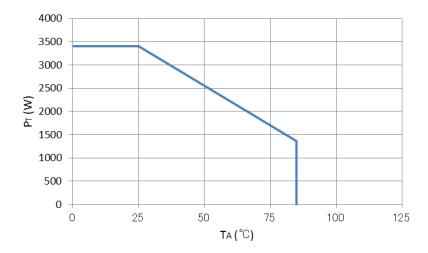
ch1:3.3V, 2A ch2: 1.8V, 0.3A

 $T_A = 25^{\circ}C$

Measured on Renesas Evaluation Board

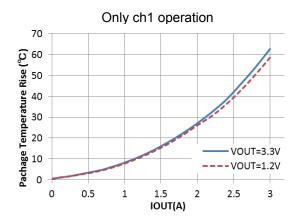


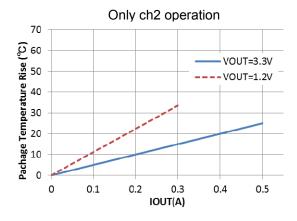
Temperature Derating Curve



Pakage Tempereture Rise vs. IOUT

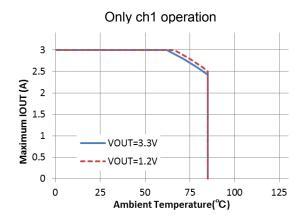
VIN=5.0V

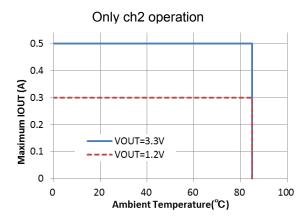




Maximum IOUT vs. Ambient Tempereture

VIN=5.0V





Note: When calculate the package temperature with both ch1 and ch2 operation, reference these data.

Control Block

SHDNB1, SHDNB2: ON/OFF Setting

SHDNB1	SHDNB2	ch1	ch2
L	L	OFF	OFF
Н	L	Start-up in order of ch1 and ch2 Stop ch1 and ch2 at the same time	
Ļ	Н	Start-up in order of ch2 and ch1 Stop ch1 and ch2 at the same time	
Н	Н	Start-up ch1 and ch Stop ch1 and ch2	

Note: L: Low level, H: High level

OFF: circuit stand-by, ON: circuit operation status

DSTB: IC Ultra Low-Power Mode Setting

DSTB	IC Operation
L	Normal operation
Н	Ultra low-power mode operation (ch1: stop, ch2: operation)

Note: L: Low level, H: High level

Output Status

V_{REG} Pin Status

SHDNB1	SHDNB2	DSTB	V_{REG}
L	L	L or H	AGND
Н	L	L	2.4 V
L	Н		
Н	Н		
Н	L	Н	AGND
L	Н		
Н	Н		

Note: L: Low level, H: High level

ch1, ch2 Output Pin Status

ch1 ⋅ ch2	ch1	ch2
Status	LOUT1	OUT2
Stop	PGND	AGND
	(Discharge circuit: On)*	(Discharge circuit: On)
Operation	Pulse (VP _{IN1} or PGND)	Set voltage

Note: Ch1 discharge circuit is "On" during ultra low-power mode.

PG Pin Status (ch1, ch2 output detect)

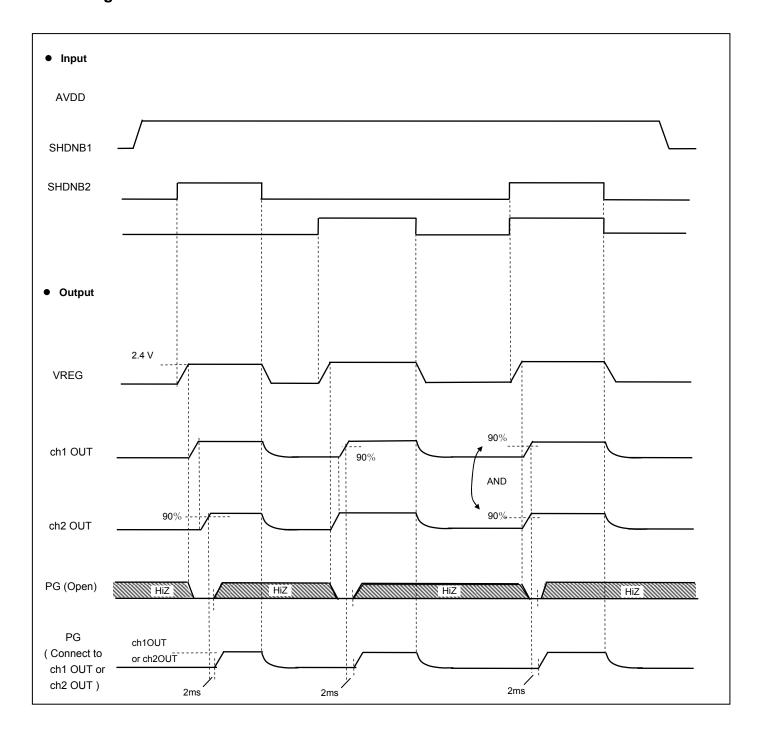
	IC Operation Status				
SHDNB Pin	DSTB Pin	ch1, ch2 Output Status	Output Status		
SHDNB1 = L SHDNB2 = L	L or H	Stop	HiZ		
SHDNB1 = H	L	ch1 or ch2 output voltage is under 90% of the set voltage	L		
or		ch1 and ch2 output voltage are over 90% of the set voltage	HiZ		
SHDNB2 = H	Н	ch1: Stop	HiZ		
		ch2: Operation (Both output voltage is over 90% of setting voltage and under 90%)			

Note: L: Low level, H: High level, HiZ: High impedance

Caution: When both ch1 and ch2 output voltage start up over 90%, there is delay time (under 2ms) before PG pin becomes HiZ.

When using power good (PG pin), connect it to ch1 or ch2 output. Recommended value of pull-up resistor is $100k\Omega$.

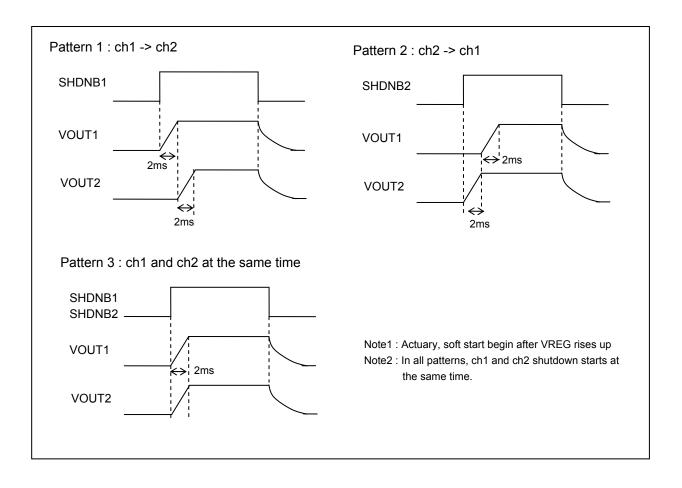
Timing Chart



Operation of Each Block (Overview)

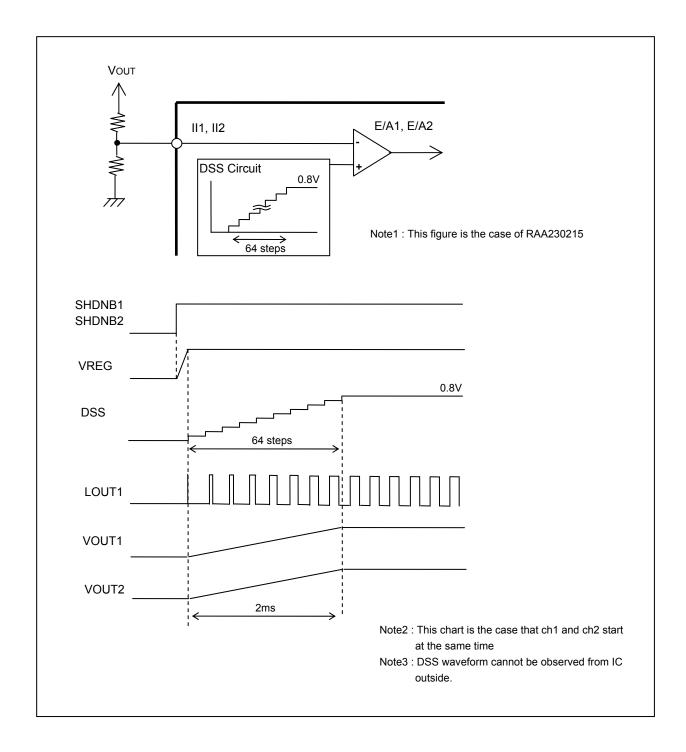
Rise up sequencer

The IC "rise up" sequence feature has 3 patterns described below. The internal "rise up" sequence capability does not need any additional external circuitry or components.



Soft start

To limit the startup inrush current and output voltage overshoot, a soft start circuit is used to ramp up the reference voltage from 0 V to its final value linearly. The soft start time are fixed for both ch1 and ch2 are 2ms(Typ.) and no additional components are needed. Soft start feature gradually increases the error amplifier (E/A) input threshold voltage by using the voltage that is generated by the digital soft start (DSS) circuit in 64 steps.

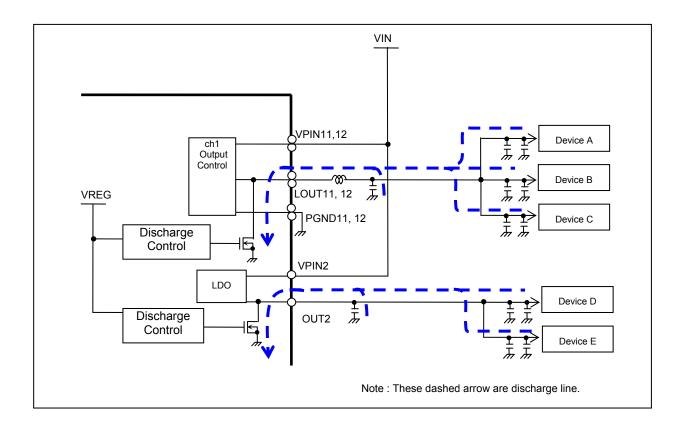


Discharge circuit

This IC has the discharge circuit for both ch1 and ch2. This enables a rapid discharge without an external MOSFET. When SHDNB pin is changed from high level to low, discharge switches of ch1 and ch2 turn on at the same time, and they discharge all capacitors which are connected to each output through LOUT1 and OUT2 pin.

When AVDD pin voltage becomes low level, discharge switches become off because there are no voltage to keep them on. The control voltage of discharge switches is VREG, and the discharge time of VREG capacitor is over 100ms when AVDD voltage fall down, so even if SHDNB pin is connected to AVDD pin, the output voltage of ch1 and ch2 can be discharged because VREG voltage level can keep the discharge switches on.

About calculation of discharge time, see page 30.



Power Good

Power Good (PG) is an open-drain output that requires a pull – up resistor (Recommended value = $100k\Omega$). PG releases when the both ch1 and ch2 FB voltage and thus the output voltage rises above 90% of nominal regulation point. The PG goes low when the FB voltage falls below 90% of the regulation point. When both SHDNB pins become low level, PG pin become high impedance (HiZ) because VREG is used for PG control and it fall down at this time. So, if PG is connected to AVDD, its status keep high level. PG pin must be connected to ch1 or ch2 output.

This function can be used for sequence signal for other devices.

Protection Circuit View

		Operat	ion Status	
Protection		Common Circuit	2 1 1	5
Circuit	Function	(V _{REG} , OSC, etc.)	Output	Reset
Short-circuit	Detect ch1 output voltage	Operation	All the output are	Change SHDNB1 pin and
protection	dropping because of		latched to OFF	SHDNB2 pin from high to low
(SCP)	short-circuit, etc.			or
*Only ch1	(Timer latch type)			Drop AV _{DD} pin input voltage
Thermal	Detect increase of IC	Operation	All the output are	under the operation stop
shutdown	internal temperature		latched to OFF	voltage (2.8 V)
circuit	(Over 150°C)			
(TSD)	(Timer latch type)			
Over current	Detect ch2 over current	Operation	ch2 output is down	Release over current status
protection			(ch1 continues	(Under the output short-circuit
(OCP)			operation)	current: 100 mA)
*Only ch2				
Under voltage	Detect dropping of AV _{DD}	Operation*1	All the outputs are	Up AV _{DD} pin input voltage
lockout circuit	(IC power supply)		stop	over the operation start
(UVLO)				voltage (2.9 V)

Note: The common circuit stops if AVDD is lower than VREG.

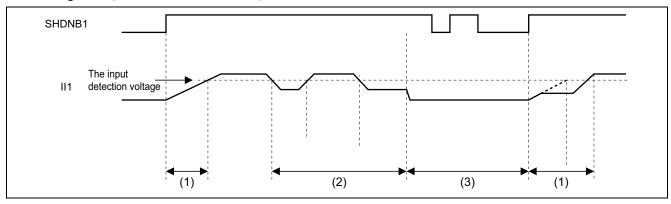
When ultra low-power mode, these protection circuits DO NOT operate.

Short-Circuit Protection Circuit (ch1)

When the voltage of ch1 drops, the voltage of the II1 pin also drops. If it falls below the input detection voltage of the short-circuit protection circuit (under 75% of output voltage), the timer circuit starts operating. And after 10 ms, all the outputs are latched to OFF. At this time, common circuits (such as the internal power supply block, and oscillator, etc.) continue operating.

When the short-circuit protection circuit is operating, to reset the latch circuit, either change the level of the SHDNB1 pin and SHDNB2 pin from high to low or drop the level of the power supply voltage (AV_{DD}) to the level below the operation stop voltage of the under voltage lockout circuit (2.8 V).

• Timing Chart (when ch1 is short circuited)



(1) At starting

- A short-circuit will not be detected while the ch1 is undergoing a soft start (that is, short-circuit protection is not triggered). If a short circuit occurs while ch1 is starting, short-circuit protection will start after the soft start time elapses following startup.
- If a short-circuit occurs in a channel that is operating while another channel is being soft-started, short-circuit protection will start immediately.
- (2) Short-circuit protection operation
 - If a short circuit is detected in ch1 (ch1 II pin voltage is lower than the input detection voltage except soft-stare period), the timer circuit starts operating. And after 10 ms, all the outputs are latched to OFF.
 - Common circuits (such as the internal power supply block, and oscillator, etc.) continue operating.
- (3) Cancelling short-circuit protection
 - To reset the latch circuit, either change the level of the SHDNB1 pin and SHDNB2 pin from high to low, or drop the level of the power supply voltage (AV_{DD}) to the operation stop voltage of the under voltage lockout circuit (2.8 V).

Thermal Shutdown Circuit (Timer Latch Type)

After overheating has been detected (shutdown temperature: 150°C or higher), the timer circuit starts operating (as same as SCP). And after 10 ms, all the outputs are latched to OFF. Common circuits (such as the internal power supply block, and oscillator, etc.) continue operating.

When the thermal shutdown circuit is operating, either change the level of the SHDNB1 pin and SHDNB2 pin from high to low, or drop the level of the power supply voltage (AV_{DD}) to the operation stop voltage of the under voltage lockout circuit (2.8 V).

When ultra low-power mode, this circuits DOES NOT operate.

Under Voltage Lockout Circuit (Auto Recovery Type)

- (1) Under voltage lockout operation
 - When the power supply voltage (AV_{DD}) falls to the operation stop voltage (2.8 V), output from all channels stops. Common circuits (such as the internal power supply block, and oscillator, etc.) continue operating.
- (2) Restoring output

Once AV_{DD} voltage is restored to the operation start voltage (2.9 V), the under voltage lockout operation is canceled and output automatically resumes. The output voltage cannot be restored while the under voltage lockout circuit is operating, not even by manipulating the SHDNB pin.

When ultra low-power mode, this circuits DOES NOT operate.

Current Limiting

Ch1 operates under the current control mode. If an overcurrent occurs, the current is limited on a pulse-by-pulse basis. If the current sensor detects an overcurrent, the current is limited and the switching operation of the Power MOSFET in the output stage stops until the next cycle.

When the ch1 current is limited, the output voltage drops. If the ch1 II pin voltage falls below the input detection voltage, the short-circuit protection circuit starts operating.

Reference data (Unless otherwise specified, $T_A = 25^{\circ}C$, $AV_{DD} = VP_{IN1} = 5.0 \text{ V}$)

Item		Symbol	Min	Тур	Max	unit	Measurement condition
Current limit	ch1 Current limet 1	I _{LIM1_1}	_	4.5	_	Α	ch1OUT 3.3V
value	ch1 Current limet 2	I _{LIM1_2}		4.5	_	Α	ch1OUT 1.2V

Note: These data are for reference and not guaranteed as specifications.

Reverse Current Protection (ch1)

Ch1 have a reverse current protection circuit. When the bottom of inductor current is under ground, low-side N-ch MOSFET of output block is stopped, and ch1 operate as diode rectification. So, consumption current at light load can be reduced.

Over Current Protection (ch2)

Ch2 have a fold back type current protection circuit. If over current occur, protection operation is started and load current is limited (output short-circuit current: 100 mA).

Peak output current depend on output voltage. When VPIN2=5V and VOUT2=3.3V, it is over 550mA.

When ultra low-power mode, this circuits DOES NOT operate.

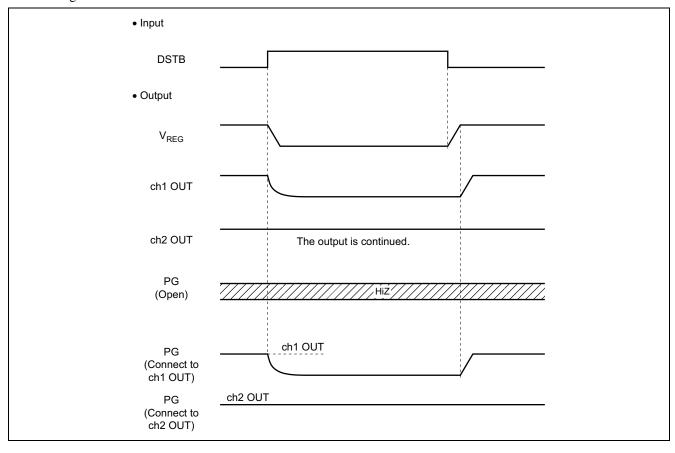


Ultra Low-Power Mode

This IC has the ultra-low power mode. By setting DSTB pin into high level, the IC operates in the ultra-low power mode, and ch2 (LDO) operates. Then the consumption current is $25~\mu A$ (TYP.) and ch1 stops. If DSTB pin is set from high level to low level, the IC operation changes to normal mode, and ch1 starts up with soft start.

When ultra low-power mode, protection circuits DOES NOT operate.

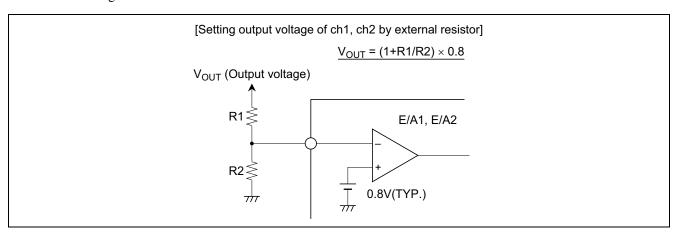
• Timing chart



Advance on Designing

Setting Output Voltage (When the output voltage is set by external resistor)

The output voltage settings are shown in the figures below. The output voltage can be calculated by the equations shown in these figures.



Examples of R1 and R2 selection

Vout	0.9V	1.0V	1.05V	1.1V	1.18V	1.2V	1.5V	1.8V	2.5V	3.3V
R1	12k	16k	16k	15k	39k	15k	24k	30k	100k	75k
R2	91k	62k	51k	39k	82k	30k	27k	24k	47k	24k

Output voltage accuracy (When the output voltage is set by external resistor)

Output voltage accuracy can be calculated by an equation below.

$$V_{OUTACC} = V_{ITHACC} + \frac{(Vout - V_{ITH})}{Vout} \times 2 \times R_{ACC}$$

V_{OUTACC} is the output voltage accuracy (%).

V_{ITHACC} is the E/A input threshold voltage accuracy (%).

V_{OUT} is the output voltage (V).

R_{ACC} is the external resistor accuracy (%).

So, each ch1 and ch2 output voltage accuracy is below.

$$V_{OUT1ACC} = 2.5 + \frac{(Vout - 0.8)}{Vout} \times 2 \times R_{ACC}$$

$$V_{OUT2ACC} = 1 + \frac{(Vout - 0.8)}{Vout} \times 2 \times R_{ACC}$$

Note: These equation don't include Vout fluctuation by load step transient.

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Handling of pins when not used

Connect unused pins as below.

Always connect AVDD pin, VPIN1 pin and VPIN2 pin with power supplies, and connect PGND1 pin and AGND with the ground.

When DSTB pin is not used:.

Pin number	Pin name	Connection
18	DSTB	AGND

When SHDNB1 pin is not used:.

Pin number	Pin name	Connection
20	SHDNB1	AGND

When SHDNB2 pin is not used:.

Pin number	Pin name	Connection
19	SHDNB2	AGND

When PG pin is not used:.

Pin number	Pin name	Connection
12	PG	AGND

Inductor selection

It is recommended to choose a inductor which ripple current (ΔIL) becomes 20 to 40 % of Iout(max).

When ΔIL increases, inductor current peak raises, so ripple of Vout gets larger and power loss increases. But, large inductor is required to lower ΔIL .

 ΔIL can be calculated by an equation below.

$$\Delta IL = \frac{(Vin - Vout)}{L} \times \frac{Vout}{Vin} \times \frac{1}{f_{SW}}$$

fsw is 1MHz.

Peak current of inductor (ILpeak) can be calculated by an equation below.

$$IL_{Peak} = I_{OUT}(MAX) + \frac{\Delta IL}{2}$$

Choose a inductor which saturation current is higher than ILpeak .

Inductor Example

ch	Output Current	Inductor	Manufacturer	Inductance (uH)	I _{TEMP} (A)	I _{SAT} (A)	Size (LxWxT, mm)
ch1	less than 1.5A	VLF504012MT-3R3M	TDK	3.3	2.4	2.1	5x4x1.2
		NRS4018T3R3MDGJ	TAIYO YUDEN	3.3	2	2.3	4x4x1.8
		744042003	WURTH	3.3	1.9	1.8	4.8x4.8x1.8
	1.5A to 3A	LTF5022T-2R2N3R2-LC	TDK	2.2	3.4	3.2	5.2x5x2.2
		NR5024T2R2NMGJ	TAIYO YUDEN	2.2	3.1	4.1	4.9x4.9x2.4
		744062002	WURTH	2.2	3.4	2.7	6.8x6.8x2.3
		LTF5022T-1R5N3R6-LC	TDK	1.5	3.4	3.2	5.2x5x2.2
		NR6020T1R5N	TAIYO YUDEN	1.5	3.2	4	6x6x2
		7440620015	WURTH	1.5	4.3	4	6.8x6.8x2.3

Note I_{TEMP} : Rated current by temperature rising I_{SAT} : Rated current by inductance loss

These inductors are examples. About inductor detail, contact each manufacturer

Output capacitor selection

Each channel of RAA23021x has a phase compensation circuit which is optimized to each operation. In order to operate stably with the phase compensation, connect the output capacitor :

DC/DC converter (ch1): over 22uF

LDO (ch2): over 10uF

Ceramic capacitor can be used for output capacitor. It has low ESR, so VOUT ripple is decreased.

VOUT ripple (Δ Vrpl) can be calculated by an equation below.

$$\Delta V_{rpl} = \Delta IL \times \left(ESR + \frac{1}{(8 \times C_{OUT} \times f_{SW})} \right)$$

Input capacitor selection

Recommended input capacitor of DC/DC converter can be calculated by an equation below. Connect the capacitor that value is over calculated one.

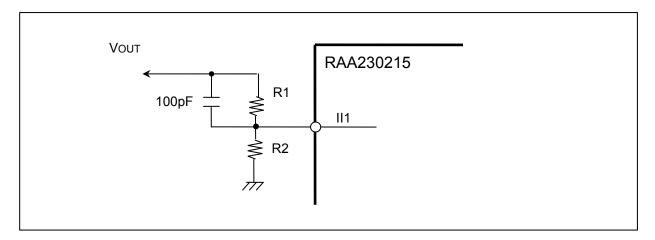
$$C_{lN} \geq \frac{I_{OUT}(MAX) \times \frac{V_{OUT}}{V_{lN}}}{\Delta V_{lN} \times f_{SW}}$$

About LDO, connect the capacitor that value is over 10uF.

Feedback capacitor

When RAA230215 (output voltage is set by external resistors) is used, connect 100pF capacitor in parallel to high side output voltage setting resistor of ch1 to improve phase characteristic.

Don't use at ch2.



Discharge time

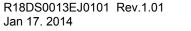
RAA23021x has discharge circuit. Discharge time can be calculated by an equation below.

$$V_{dc} = V_{OUT} \times e^{-\frac{t_{dc}}{C_{ALL} \times R_{ondc}}}$$

 V_{dc} is a voltage after tdc(s).

 C_{ALL} is sum of all capacitance which are connected to the output of RAA23021x (output capacitor, bypass capacitor around MCU, etc.).

R_{ondc} is on resistance of discharge circuit.





Notes on Use

Connection of power input pin

Be sure to apply the same voltage to AV_{DD} pin and VP_{IN11} pin. VP_{IN2} input voltage must be same or less than AV_{DD} .

PG Connection

When using power good (PG pin), connect it to ch1 or ch2 output. If PG is connected to AV_{DD} , PG outputs high (AV_{DD}) when SHDNB1 and SHDNB2 is low (because PG is high impedance when SHDNB1 and SDHNB2 is low).

Protection Circuit at Ultra Low-Power Mode

When ultra low-power mode, all protection circuits DO NOT operate.

Actual Pattern Wiring

To actually perform pattern wiring, separate the ground of the control signals (AGND) from the ground of the power signals (PGND), so that these signals do not have common impedance as much as possible. In addition, lower the high-frequency impedance by using a capacitor, so that noise is not superimposed on the V_{REG} pin.

Connection of Exposed PAD

RAA23021x has an exposed pad on the bottom to improve radiation performance. On the mounting board, connect to AGND.

Connection of Component Ground

When connecting a component to ground, connect to the ground below.

Component	Connect Ground
ch1 input capacitor, ch1 output capacitor	PGND
ch2 input capacitor, ch2 output capacitor	AGND
ch1 output voltage setting resistor (low side)	
ch2 output voltage setting resistor (low side)	
VREG capacitor	

Fixed Usage of Control Input Pin

When using fixed input pins SHDNB1, SHDNB2, DSTB input pins, connect each input to the pins listed below.

	Connect Pin				
Input Pin	Fixed to Low Level	Fixed to High Level			
SHDNB1	AGND	AV_DD			
SHDNB2	AGND	AV_DD			
DSTB	AGND	AV_DD			

Connection of Test Pin

Connect each test pin to the pins listed below.

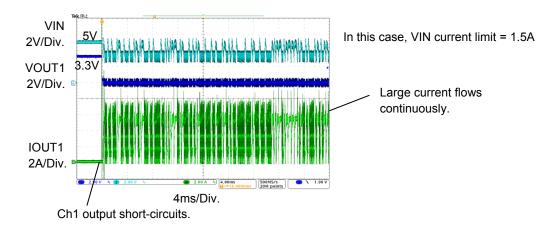
Test Pin	Connect Pin
TEST1	AGND
TEST2	VREG
TEST3	OPEN



The case short-circuit is not protected.

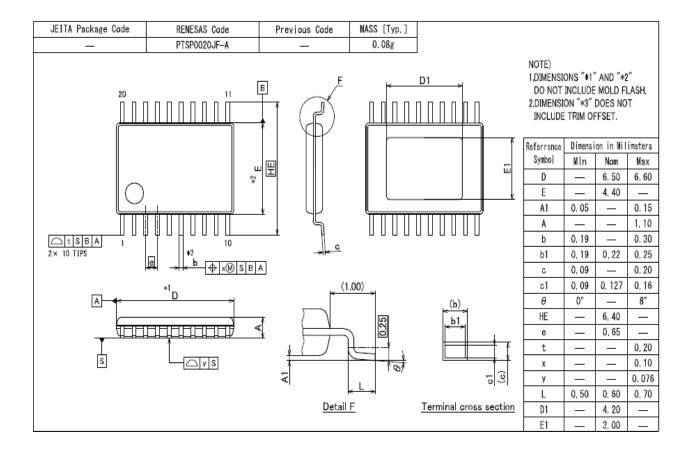
If a power supply of RAA23021x has current limit which is under ch1 current limit 4.5A (Typ.), the voltage and thus AVDD falls when ch1 output short-circuits. If it becomes under operation stop voltage of UVLO (Typ. 2.8V), all the output voltage are stopped. Then ch1 short-circuit is stopped, so AVDD recovers. After it becomes above operation start voltage of UVLO (Typ. 2.9V), ch1 and ch2 output are restored, and ch1 short-circuits again. A large current may flow continuously by repeating these operations.

To avoid devices destruction by the large current, set the power supply current limit higher or use a fuse into the power supply line.



Package Dimensions

20-pin HTSSOP



Revision History

RAA23021x Datasheet

		Description	
Rev.	Date	Page Summary	
1.01	Jan 17, 2014	-	First Edition of datasheet issued

NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pullup power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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